



ShenzhenTaimaoTechnology Co.,Ltd.

TO-92 Plastic-Encapsulate Transistors

2N5832 TRANSISTOR (NPN)

FEATURES

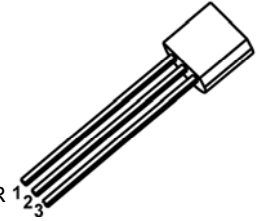
- General Purpose Switching Application

TO – 92

1. EMITTER

2. BASE

3. COLLECTOR



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	600	mA
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	140			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=120\text{V}, I_E=0$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.05	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=10\text{mA}$	175		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			1	V
Base-emitter voltage	V_{BE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$			0.8	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			4	pF
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=1\text{mA}, f=100\text{MHz}$	100			MHz